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AccelStack: A Cost-Driven Analysis of 3D-Stacked LLM Accelerators

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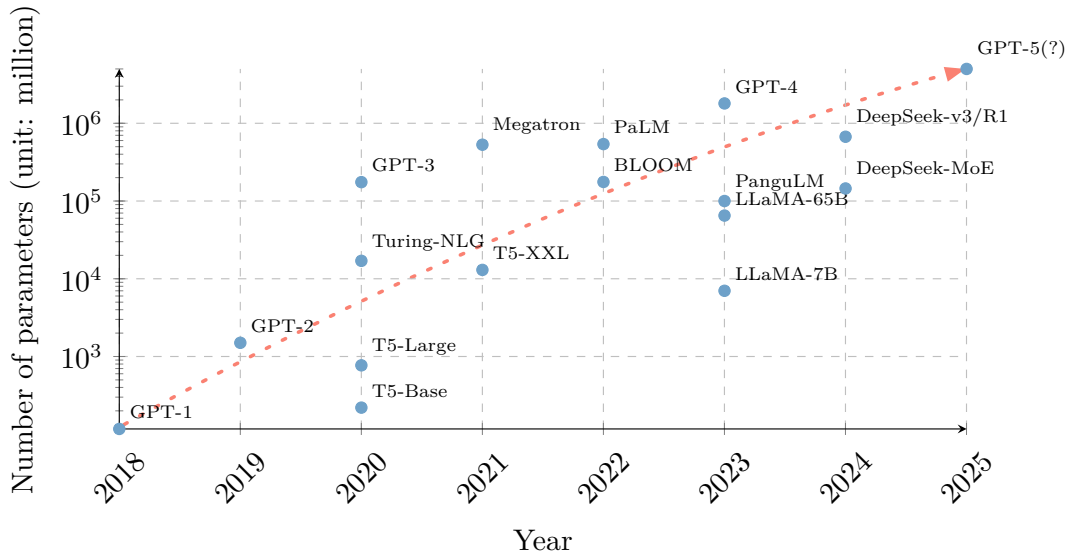
² Tsinghua University

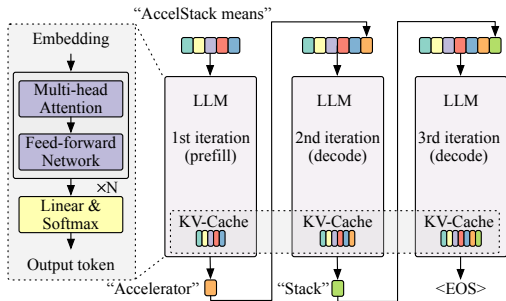
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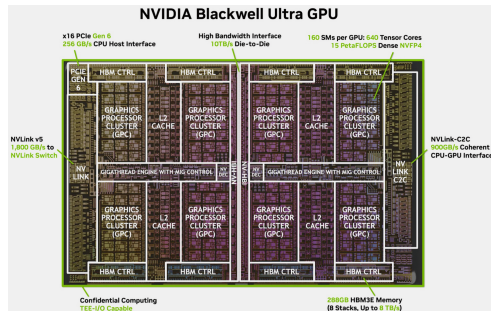
- ① Introduction
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- ③ Experiments
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Introduction





Overview of LLM inference.



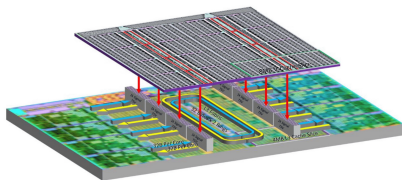
NVIDIA B200 die shot.

Innovations in LLM accelerators:

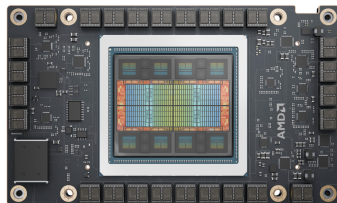
- Compute → 3D cube unit (Huawei HiSilicon), systolic arrays (Google), tensor cores (NVIDIA).
- Memory → High-bandwidth memory.
- Interconnect → Advanced 2.5D packaging.

Hybrid Bonding

It can stack chips with bumpless connections, *e.g.*, Cu-Cu bond¹.



AMD 3D V-Cache.



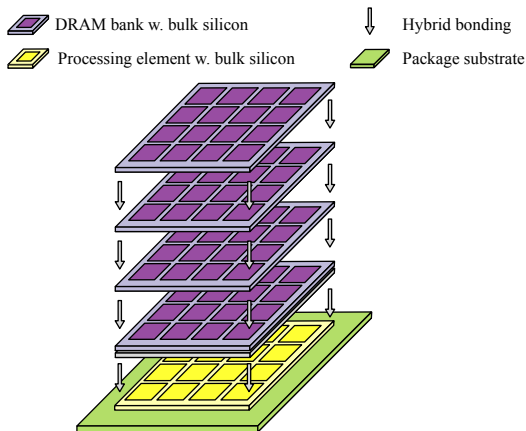
AMD MI355X.

Compared to previous technology (microbump and 2.5D advanced packaging)²:

- 5 ~ 50× improvement in pitches → Higher GB/s/mm².
- 5 ~ 20× improvement in die-to-die distance → Smaller gate-to-gate delay.

¹DB Ingerly et al. (2019). “Foveros: 3D Integration and the Use of Face-to-Face Chip Stacking for Logic Devices”. In: *IEEE International Electron Devices Meeting (IEDM)*. IEEE, pp. 19–6.

²John Wu et al. (2022). “3D V-Cache: the Implementation of a Hybrid-Bonded 64MB Stacked Cache for a 7nm x86-64 CPU”. In: *IEEE International Solid-State Circuits Conference (ISSCC)*. vol. 65.



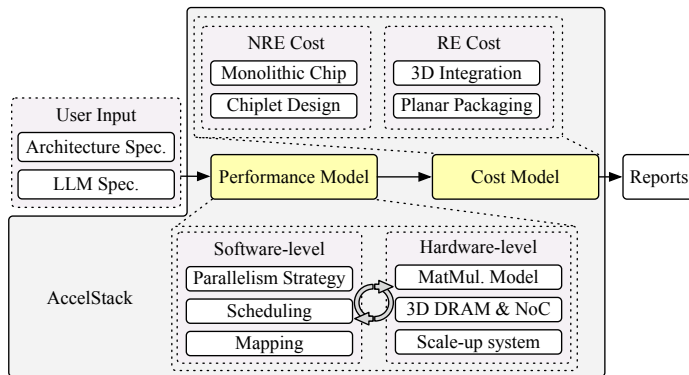
Problems:

- Performance: superiority over traditional LLM accelerators?
- Manufacturing cost: economic feasibility?

Can we decide on an investment in high-volume manufacturing (HVM) of the 3D-stacked LLM accelerators?

A possible architecture landscape in the future.

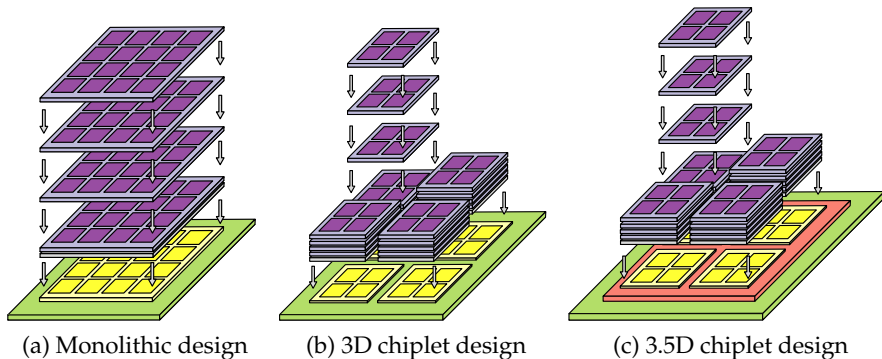
AccelStack



Overview of AccelStack.

In the following, we discuss:

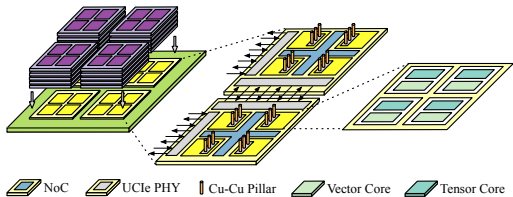
- Focused 3D-stacked architecture assumptions.
- Performance model.
- Cost model.



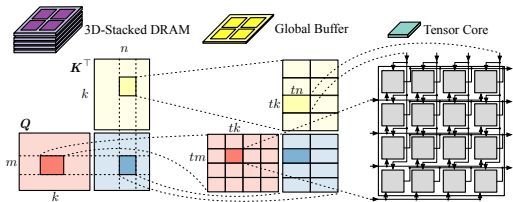
Chipletized versions of the architecture landscape.

- Chiplet-to-chiplet interconnections are modeled according to the UCIE specification³.
- We model CoWoS, EMIB, and MCM packaging techniques.

³Universal Chiplet Interconnect Express 2.0 Specification (2024).



(a) The microarchitecture of the 3D chiplet design.



(b) Two-level loop tiling for GEMM operations.

The scale-up system is modeled with a Clos-based topology⁴.

The tensor core is a $p \times p$ array.

P denotes the number of outputs per cycle.

α is the utilization.

B is the link bandwidth.

- Computing latency:

$$t_{\text{comp}} = \frac{m + tm - 1}{tm} \cdot \frac{n + tn - 1}{tn} \cdot \frac{k + tk - 1}{tk} \cdot \frac{2 \cdot (tm + p - 1) \cdot (tn + p - 1) \cdot tk}{p^2 \cdot \alpha \cdot P}. \quad (1)$$

- Communication latency:

$$t_{\text{comm}} = \frac{V}{B} + l + o, \quad V = \left\lceil \frac{n}{\text{payload}} \right\rceil \cdot \text{flit}. \quad (2)$$

⁴Pengfei Zuo et al. (2025). "Serving Large Language Models on Huawei CloudMatrix384". In: *arXiv preprint arXiv:2506.12708*.



$$C = C_{\text{NRE}} + C_{\text{RE}}, \quad (3)$$

We use a first-order approximation to evaluate C_{NRE} .

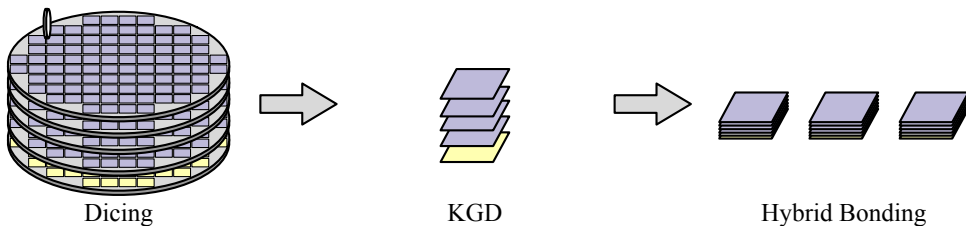
Monolithic design:

$$C_{\text{NRE}} = \left(\sum_{m_i \in \text{chip}} \alpha_{m_i} A_{m_i} \right) + \beta_{\text{chip}} A_{\text{chip}} + C_{\text{fixed}}. \quad (4)$$

Chiplet design:

$$C_{\text{NRE}} = \sum_{m_i \in M} \alpha_{m_i} A_{m_i} + \left(\sum_{c \in \text{chip}} \beta_c A_c + C_{\text{fixed}_c} \right) + C_{\text{fixed}}. \quad (5)$$

α_{m_i} is a cost coefficient. A is the silicon area. β accounts for physical design and verification efforts. C_{fixed} refers to the requisite fixed costs.

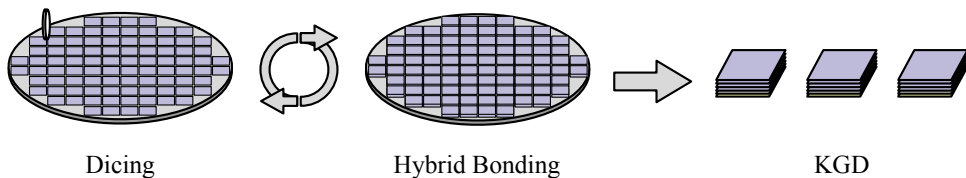


Die-on-die manufacturing flow (DoD).

$$C_{3D} = \frac{\sum_{i=1}^n C_{\text{die}_i} + (n-1)C_{\text{DoD}}}{\prod_{i=1}^{n-1} Y_{\text{DoD}}}, \quad (6)$$

where

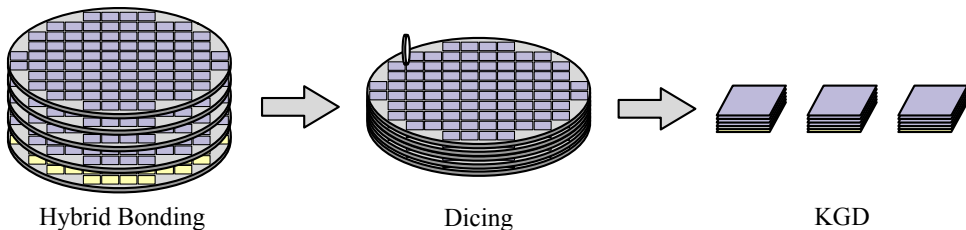
$$C_{\text{die}_i} = \left(\frac{C_{\text{wafer}}}{N_{\text{die}}} + C_{\text{test}} + C_{\text{misc.}} \right) / Y_{\text{die}}. \quad (7)$$



Die-on-wafer manufacturing flow (DoW).

$$C_{3D} = \left(\frac{C_{\text{logic wafer}} + C_{\text{DoW}}}{N_{\text{logic}}} + C_{\text{DRAM}_{i+1}} + C_{\text{test}} + C_{\text{misc.}} \right) / (Y_{\text{logic}} \cdot Y_{\text{DoW}}),$$
$$C_{\text{DRAM}_{i+1}} = \left(\frac{C_{\text{DRAM wafer}} + C_{\text{DRAM}_i} + C_{\text{DoW}}}{N_{\text{DRAM}}} + C_{\text{test}} + C_{\text{misc.}} \right) / Y_{\text{DoW}}.$$

(8)



Wafer-on-wafer manufacturing flow (WoW).

$$C_{3D} = \left(\frac{\sum_{i=1}^n C_{\text{wafer}_i} + (n-1) \cdot C_{\text{WoW}}}{\min \{N_{\text{logic}}, N_{\text{DRAM}}\}} + C' \right) / Y', \quad (9)$$
$$Y' = Y_{\text{logic}} \cdot Y_{\text{DRAM}} \cdot \prod_{i=1}^{n-1} Y_{\text{WoW}}.$$



CoWoS, EMIB, and MCM packaging:

$$\begin{aligned} C_{\text{package}} = & C_{\text{raw package}} + \\ & C_{\text{interposer}} \cdot \left(\frac{1}{Y_1 \cdot Y_2^n \cdot Y_3} - 1 \right) + \\ & C_{\text{substrate}} \cdot \left(\frac{1}{Y_3} - 1 \right) + \\ & C_{3D} \cdot \left(\frac{1}{Y_2^n \cdot Y_3} - 1 \right). \end{aligned} \tag{10}$$

Y_1 is the yield of the interposer or bridge structure.

Y_2 is the bonding yield of chips.

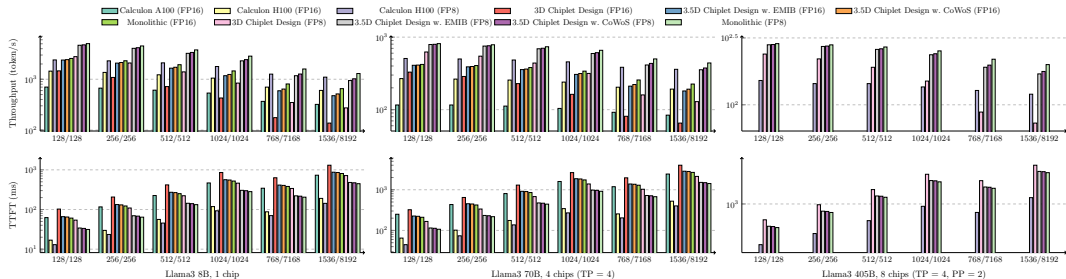
Y_3 is the bonding yield of the interposer or bridge structure.

Experiments

Architecture configurations

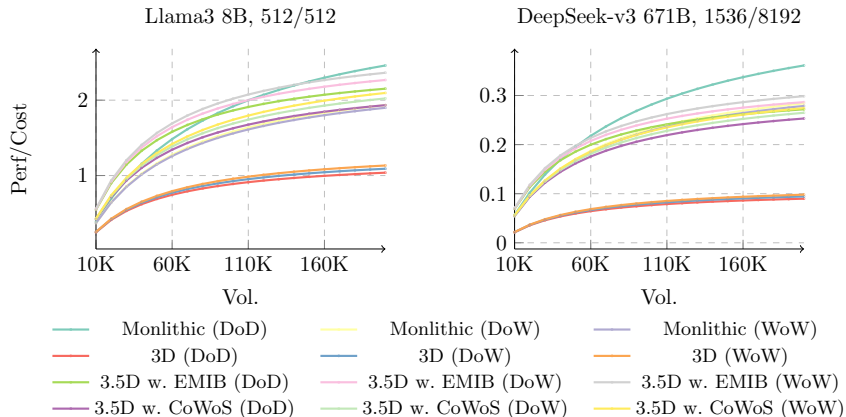
Metric	Value
Silicon area of the monolithic design	$32 \times 25 \text{ mm}^2$
# of DRAM stacks	4
Total DRAM capacity	64 GB
Aggregate DRAM bandwidth	9.6 TB/s
# of processing elements (PEs)	16
Computing power	786 TFLOPS@FP8, 393 TFLOPS@FP16
NoC bisection bandwidth of the monolithic design	1.5 TB/s
NoC bisection bandwidth of 3D chiplet design w. CoWoS	1.1 TB/s
NoC bisection bandwidth of 3D chiplet design w. EMIB	1.0 TB/s
NoC bisection bandwidth of 3D chiplet design (MCM)	255.0 GB/s
Price ratio (DoD:DoW:WoW)	4 : 2 : 1
Hybrid bonding yield	0.95

Compare w. A100/H100 Simulation Results



Compare w. A100 & H100 simulation results.

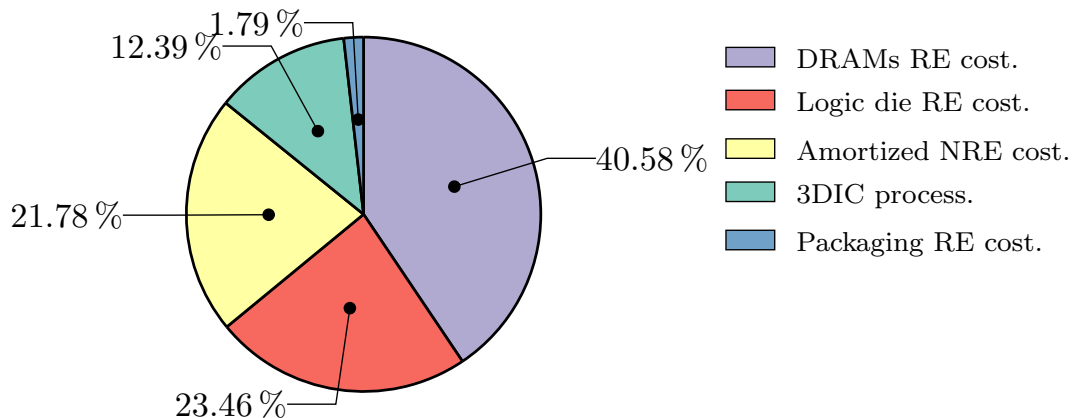
- The monolithic design vs. A100 (FP16) and H100 (FP8): $7.17\times$ and $2.09\times$ higher token/s.
- Slow-thinking (7 ~ 8K output tokens), 3D-stacked design vs. H100 (FP8): $1.36\times$ greater throughput.



Performance-per-cost comparison.

For Llama3:

- The 3.5D chiplet design with EMIB using the WoW is the winner for shipment volumes below 140K (approximately 3500 logic wafers).
- Monolithic design with DoD is the winner for shipments more than 140K.



Cost breakdown for monolithic design with WoW under 200K shipment volumes.

- Much of the cost contributes to the 3D-stacked DRAM.

Conclusion



- A performance model for 3D-stacked LLM accelerators.
- A cost model supports DoD, DoW, and WoW hybrid bonding manufacturing flows.
- 3D-stacked accelerators can achieve up to $7.17\times$ and $2.09\times$ faster inference than A100 (FP16) and H100 (FP8) simulation results, with chiplet-based designs reducing recurring engineering costs by 38.09% versus monolithic implementations.
- Open-source address: <https://github.com/baichen318/accel-stack>!

THANK YOU!



- DB Ingerly et al. (2019). “Foveros: 3D Integration and the Use of Face-to-Face Chip Stacking for Logic Devices”. In: *IEEE International Electron Devices Meeting (IEDM)*. IEEE, pp. 19–6.
- Universal Chiplet Interconnect Express 2.0 Specification* (2024).
<https://www.uciexpress.org/specifications>.
- John Wu et al. (2022). “3D V-Cache: the Implementation of a Hybrid-Bonded 64MB Stacked Cache for a 7nm x86-64 CPU”. In: *IEEE International Solid-State Circuits Conference (ISSCC)*. Vol. 65. IEEE, pp. 428–429.
- Pengfei Zuo et al. (2025). “Serving Large Language Models on Huawei CloudMatrix384”. In: *arXiv preprint arXiv:2506.12708*.